

BC558BRLG Datasheet



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DiGi Electronics Part Number BC558BRLG-DG

Manufacturer onsemi

Manufacturer Product Number BC558BRLG

Description TRANS PNP 30V 0.1A TO92

Detailed Description Bipolar (BJT) Transistor PNP 30 V 100 mA 360MHz 6

25 mW Through Hole TO-92 (TO-226)



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BC558

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
BC558BRLG	onsemi
Series:	Product Status:
	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
PNP	100 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
30 V	650mV @ 5mA, 100mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ lc, Vce:
100nA	180 @ 2mA, 5V
Power - Max:	Frequency - Transition:
625 mW	360MHz
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Through Hole
Package / Case:	Supplier Device Package:
TO-226-3, TO-92-3 Long Body (Formed Leads)	TO-92 (TO-226)
Base Product Number:	

Environmental & Export classification

Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
FAR99	8541.21.0075

Amplifier Transistors

PNP Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage BC5 BC5 BC5	557	-65 -45 -30	Vdc
Collector - Base Voltage BC5 BC5 BC5	557	-80 -50 -30	Vdc
Emitter - Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous – Peak	I _C	-100 -200	mAdc
Base Current – Peak	I _{BM}	-200	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

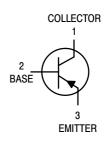
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

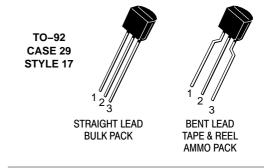
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



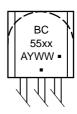
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MARKING DIAGRAM



xx = 6B, 7A, 7B, 7C, or 8B A = Assembly Location

Y = Year WW = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS			•		•	•
Collector-Emitter Breakdown Voltage (I _C = -2.0 mAdc, I _B = 0)	BC556 BC557 BC558	V _{(BR)CEO}	-65 -45 -30	_ _ _	- - -	V
Collector – Base Breakdown Voltage (I _C = –100 μAdc)	BC556 BC557 BC558	V _{(BR)CBO}	-80 -50 -30	_ _ _	- - -	V
Emitter – Base Breakdown Voltage ($I_E = -100 \mu Adc, I_C = 0$)	BC556 BC557 BC558	$V_{(BR)EBO}$	-5.0 -5.0 -5.0	- - -	- - -	V
Collector-Emitter Leakage Current (V _{CES} = -40 V) (V _{CES} = -20 V) (V _{CES} = -20 V, T _A = 125°C)	BC556 BC557 BC558 BC556 BC557 BC557	I _{CES}	- - - -	-2.0 -2.0 -2.0 - -	-100 -100 -100 -4.0 -4.0 -4.0	nA μA
ON CHARACTERISTICS				1		
DC Current Gain $(I_C = -10 \ \mu Adc, \ V_{CE} = -5.0 \ V)$ $(I_C = -2.0 \ mAdc, \ V_{CE} = -5.0 \ V)$	A Series Device B Series Devices C Series Devices BC557 A Series Device	h _{FE}	- - - 120 120	90 150 270 – 170	- - - 800 220	-
$(I_C = -100 \text{ mAdc}, V_{CE} = -5.0 \text{ V})$	B Series Devices C Series Devices A Series Device B Series Devices C Series Devices		180 420 - - -	290 500 120 180 300	460 800 - - -	
		V _{CE(sat)}	- - -	-0.075 -0.3 -0.25	-0.3 -0.6 -0.65	V
Base – Emitter Saturation Voltage ($I_C = -10$ mAdc, $I_B = -0.5$ mAdc) ($I_C = -100$ mAdc, $I_B = -5.0$ mAdc)		V _{BE(sat)}	_ _	-0.7 -1.0	- -	V
Base–Emitter On Voltage ($I_C = -2.0 \text{ mAdc}$, $V_{CE} = -5.0 \text{ Vdc}$) ($I_C = -10 \text{ mAdc}$, $V_{CE} = -5.0 \text{ Vdc}$)		V _{BE(on)}	-0.55 -	-0.62 -0.7	-0.7 -0.82	V
SMALL-SIGNAL CHARACTERISTICS						
Current – Gain – Bandwidth Product ($I_C = -10$ mA, $V_{CE} = -5.0$ V, $f = 100$ MHz)	BC556 BC557 BC558	f _T	_ _ _	280 320 360	- - -	MHz
Output Capacitance $(V_{CB} = -10 \text{ V}, I_{C} = 0, f = 1.0 \text{ MHz})$		C _{ob}	_	3.0	6.0	pF
Noise Figure (I _C = -0.2 mAdc, V _{CE} = -5.0 V, R _S = 2.0 k Ω , f = 1.0 kHz, Δ f = 200 Hz)	BC556 BC557 BC558	NF	- - -	2.0 2.0 2.0	10 10 10	dB
Small–Signal Current Gain ($I_C = -2.0 \text{ mAdc}, V_{CE} = 5.0 \text{ V}, f = 1.0 \text{ kHz}$)	BC557 A Series Device B Series Devices C Series Devices	h _{fe}	125 125 240 450	- - - -	900 260 500 900	-
-						

^{1.} $I_C = -10$ mAdc on the constant base current characteristics, which yields the point $I_C = -11$ mAdc, $V_{CE} = -1.0$ V.

BC557/BC558

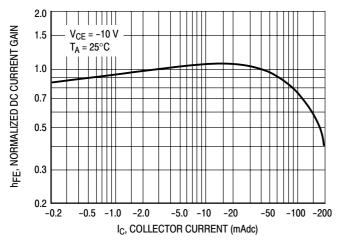


Figure 1. Normalized DC Current Gain

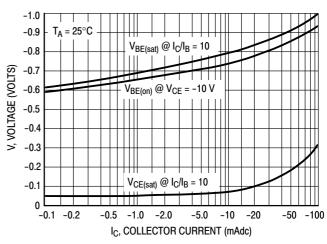


Figure 2. "Saturation" and "On" Voltages

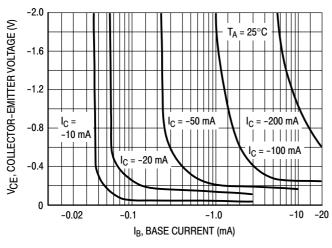


Figure 3. Collector Saturation Region

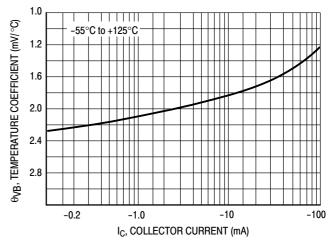


Figure 4. Base-Emitter Temperature Coefficient

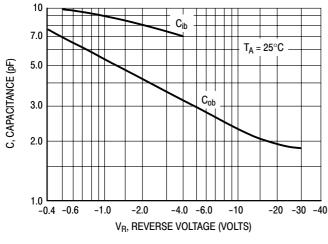


Figure 5. Capacitances

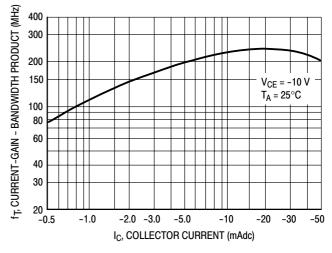


Figure 6. Current-Gain - Bandwidth Product

BC556

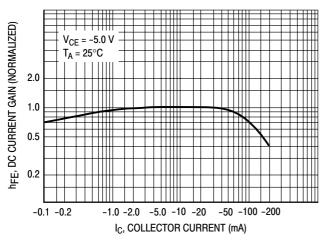


Figure 7. DC Current Gain

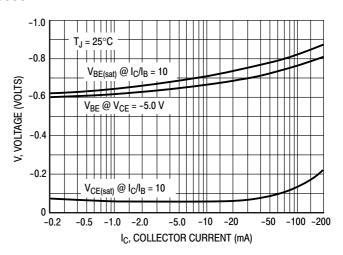


Figure 8. "On" Voltage

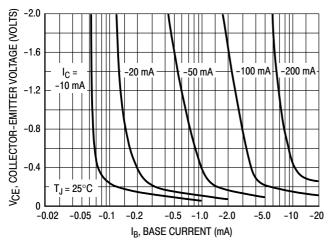


Figure 9. Collector Saturation Region

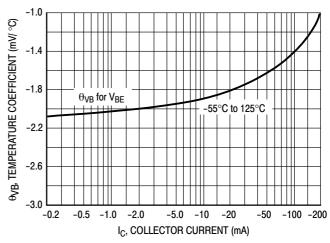


Figure 10. Base-Emitter Temperature Coefficient

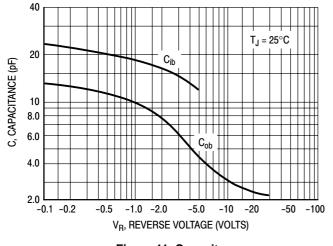


Figure 11. Capacitance

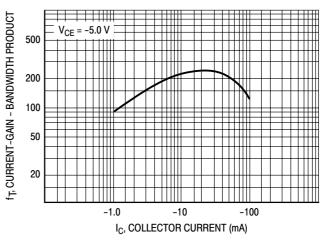


Figure 12. Current-Gain - Bandwidth Product

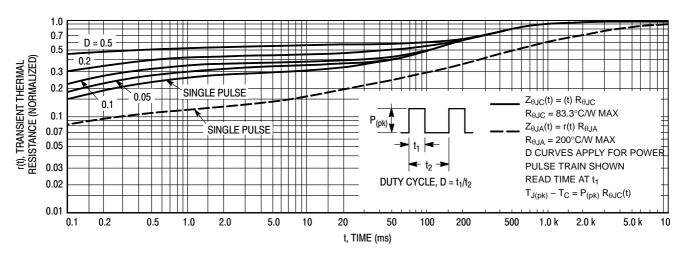


Figure 13. Thermal Response

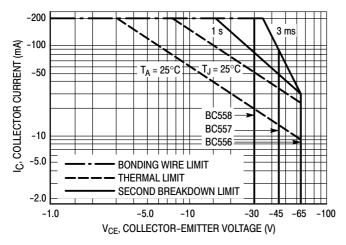


Figure 14. Active Region - Safe Operating Area

The safe operating area curves indicate I_C-V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 14 is based upon $T_{J(pk)} = 150^{\circ}C$; T_{C} or T_{A} is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 13. At high case or ambient temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

ORDERING INFORMATION

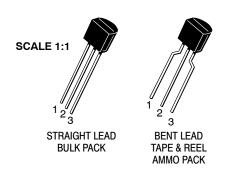
Device	Package	Shipping [†]
BC556BG	TO-92 (Pb-Free)	5000 Units / Bulk
BC556BZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC557AZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC557BG	TO-92 (Pb-Free)	5000 Units / Bulk
BC557BRL1	TO-92	2000 / Tape & Reel
BC557BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
BC557BZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC557CG	TO-92 (Pb-Free)	5000 Units / Bulk
BC557CZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC558BRLG	TO-92 (Pb-Free)	2000 / Tape & Reel
BC558BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
BC558BZL1G	TO-92 (Pb-Free)	2000 / Ammo Box

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



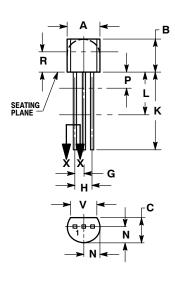
MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS



TO-92 (TO-226) CASE 29-11 **ISSUE AM**

DATE 09 MAR 2007



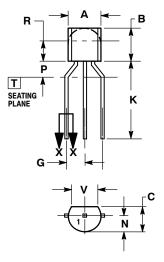
STRAIGHT LEAD **BULK PACK**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI

- Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
 CONTOUR OF PACKAGE BEYOND DIMENSION R
 IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



BENT LEAD TAPE & REEL AMMO PACK



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER

- AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS					
DIM	MIN	MAX				
Α	4.45	5.20				
В	4.32	5.33				
С	3.18	4.19				
D	0.40	0.54				
G	2.40	2.80				
J	0.39	0.50				
K	12.70					
N	2.04	2.66				
P	1.50	4.00				
R	2.93					
V	3.43					

STYLES ON PAGE 2

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TO-92 (TO-226) CASE 29-11 ISSUE AM

DATE 09 MAR 2007

STYLE 1: PIN 1. 2. 3.	EMITTER BASE COLLECTOR	STYLE 2: PIN 1. 2. 3.	BASE EMITTER COLLECTOR	STYLE 3: PIN 1. 2. 3.	ANODE ANODE CATHODE	STYLE 4: PIN 1. 2. 3.	CATHODE CATHODE ANODE	STYLE 5: PIN 1. 2. 3.	DRAIN SOURCE GATE
STYLE 6: PIN 1. 2. 3.	GATE SOURCE & SUBSTRATE DRAIN	STYLE 7: PIN 1. 2. 3.	SOURCE DRAIN GATE	STYLE 8: PIN 1. 2. 3.	DRAIN GATE SOURCE & SUBSTRATE	STYLE 9: PIN 1. 2. 3.	BASE 1 EMITTER BASE 2	STYLE 10: PIN 1. 2. 3.	CATHODE GATE ANODE
STYLE 11: PIN 1. 2. 3.	ANODE CATHODE & ANODE CATHODE	STYLE 12: PIN 1. 2. 3.	MAIN TERMINAL 1 GATE MAIN TERMINAL 2	STYLE 13: PIN 1. 2. 3.	ANODE 1 GATE CATHODE 2	STYLE 14: PIN 1. 2. 3.	EMITTER COLLECTOR BASE	STYLE 15: PIN 1. 2. 3.	ANODE 1 CATHODE ANODE 2
STYLE 16: PIN 1. 2. 3.	ANODE GATE CATHODE	STYLE 17: PIN 1. 2. 3.	COLLECTOR BASE EMITTER	STYLE 18: PIN 1. 2. 3.	ANODE CATHODE NOT CONNECTED	STYLE 19: PIN 1. 2. 3.	GATE ANODE CATHODE	STYLE 20: PIN 1. 2. 3.	NOT CONNECTED CATHODE ANODE
STYLE 21: PIN 1. 2.	COLLECTOR EMITTER	STYLE 22: PIN 1.	SOURCE GATE	STYLE 23: PIN 1. 2.	GATE SOURCE DRAIN	STYLE 24: PIN 1. 2.	EMITTER	STYLE 25: PIN 1. 2.	MT 1
	Vcc	STYLE 27: PIN 1. 2. 3.	MT SUBSTRATE MT	STYLE 28: PIN 1. 2. 3.	CATHODE ANODE GATE	PIN 1.	NOT CONNECTED ANODE CATHODE	PIN 1. 2.	DRAIN GATE
2.	GATE DRAIN SOURCE	STYLE 32: PIN 1. 2. 3.	BASE COLLECTOR EMITTER	STYLE 33: PIN 1. 2. 3.	RETURN INPUT OUTPUT	STYLE 34: PIN 1. 2. 3.	INPUT GROUND LOGIC	PIN 1.	GATE

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